In The Claims:

Please amend claims 1 and 7 as follows:

1. (Amended) A process for forming a silicon oxide layer of non-uniform thickness on a surface of one and the same silicon substrate, comprising:

a) implanting in predetermined regions of the substrate a chemical species at a concentration which increases the rate of oxidation of the substrate, wherein the chemical species comprises neon or helium; and

b) growing a silicon oxide layer of non-uniform thickness by oxidizing the surface of the substrate.

Please amend claim 7 as follows:

7. (Amended) The process as claimed in claim 6, wherein growing the silicon oxide layer comprises an oxidation step in a furnace at a temperature of at least 300°C and in an oxidizing atmosphere.

Please cancel claims 2, 8, 10 and 13 without prejudice.

Please add the following claim:

17. (New) A method of forming a MOS transistor grid comprising:

forming a silicon oxide layer of non-uniform thickness on a surface a silicon substrate, wherein forming the silicon oxide layer comprises: